



30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

70 A

Features

- R_{DS(ON)}, V_{GS}@10V, I_D@10A<3.8mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@5A<5.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams

DFN3333-8L

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V _{DS}	30		
Gate-Source Voltage		V _{GS}	<u>+</u> 20		
Continuous Drain Current(Note 4)	T _C =25°C	- I _D -	70		
	Tc=100°C		44	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I_{DM}	280		
Power Dissipation	Tc=25°C	Po	39	10/	
	T _C =100°C		15.6	W	
Continuous Drain Current(Note 4)	T _A =25°C	I _D	16		
	T _A =70°C		13	Α	
Power Dissipation	T _A =25°C	ı	2	10/	
Power Dissipation	T _A =70°C	Pb	1.3	W	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{θJC}	3.21	°C/W	
	Junction to Ambient	R _{0JA}	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1	1.6	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A	-	3.3	3.8	mΩ	
		V _{GS} =4.5V, I _D =5A	-	5	5.5		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 6)							
Total Gate Charge	Q_g	V _{DS} =15V, I _D =24A, V _{GS} =4.5V ^(Note 2,3)	-	23	-	nC	
Gate-Source Charge	Q_{gs}		-	8	-		
Gate-Drain Charge	Q_{gd}		-	9	-		
Input Capacitance	Ciss	\/ OF\/ \/ O\/	-	2436	-	pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	306	-		
Reverse Transfer Capacitance	Crss	I = IIVII IZ	-	196	-		
Turn-On Delay Time	td _(on)	\/ 45\/ 45\	-	32	-		
Turn-On Rise Time	tr	V _{DS} =15V, I _D =15A, V _{GS} =10V, R _G =1Ω (Note 2.3)	-	169	-	ns	
Turn-Off Delay Time	td _(off)		-	232	-		
Turn-Off Fall Time	t f	(1333 =,3)	-	170	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	l _a		-	-	70	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.66	1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

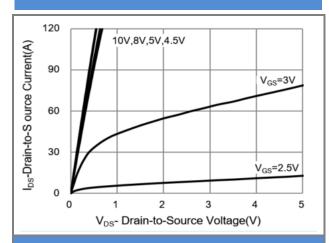


Fig.1 On-Region Characteristics

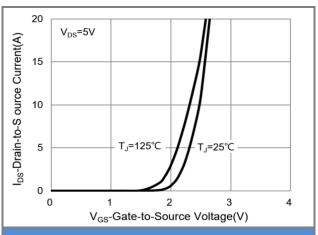


Fig.2 Transfer Characteristics

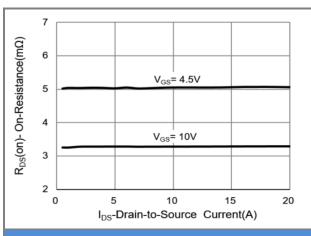


Fig.3 On-Resistance vs. Drain Current

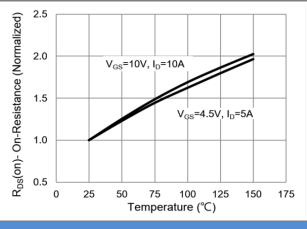


Fig.4 On-Resistance vs. Junction temperature

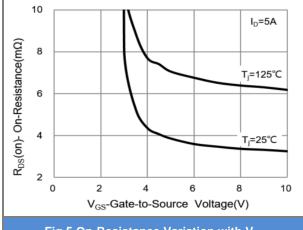


Fig.5 On-Resistance Variation with V_{GS}

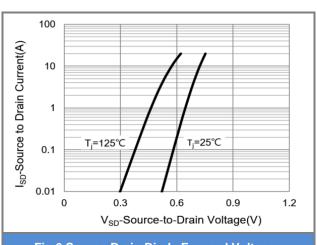


Fig.6 Source-Drain Diode Forward Voltage



1.2

1.0

0.8

0.6

0.4

0

V_{TH}-G-S Vriance



PJQ4402P-AU

TYPICAL CHARACTERISTIC CURVES

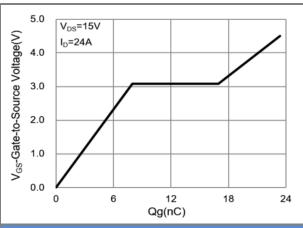


Fig.7 Gate-Charge Characteristics

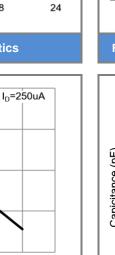


Fig.9 Threshold Voltage Variation with Temperature

Temperature (°C)

100

125

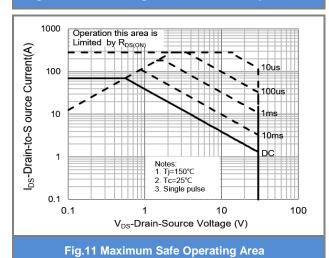


Fig.8 Breakdown Voltage Variation vs. Temperature

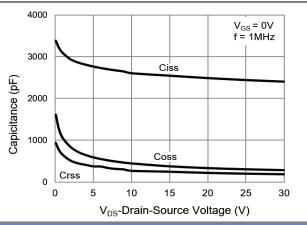


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

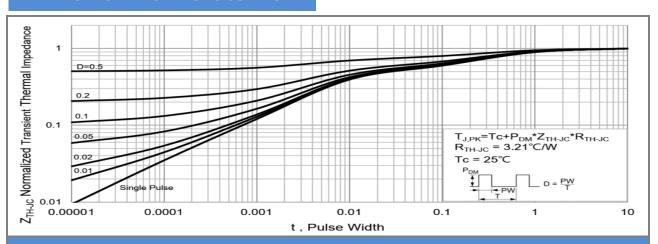


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

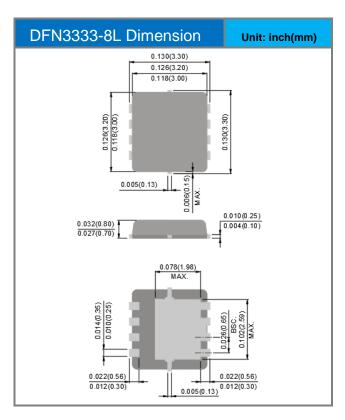


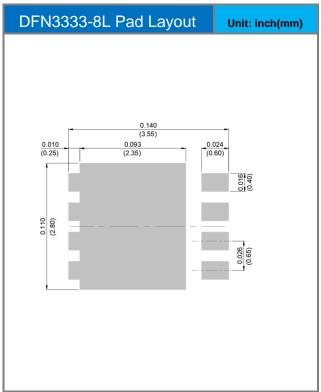


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4402P-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4402	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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